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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application Serial No. 09,388,826
Filing Date September 1, 1999
Inventor Weimin Li, et al.
Assignee Micron Technology, Inc.
Group Art Unit 2813
Examiner E. Kielin
Attorney's Docket No. MI22-1208
Title: Low k Interlevel Electric Layer Fabrication Methods

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

References -- See Attached Form PTO-1449

The attached form PTO-1449 is submitted in compliance with 37 CFR § 1.56.
Copies of the cited prior art references are attached. No admission is made regarding whether the submitted references are prior art.

Citation of these references is respectfully requested.

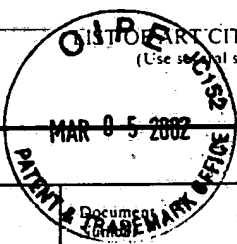
Respectfully submitted,

Date: Sep 25, 2001

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Sheet 1 of 5

200 Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. MI22-1208		SERIAL NO. 09/388,826	
 ART CITED BY APPLICANT (Use separate sheets if necessary)				APPLICANT Weimin Li et al.		GROUP 2813	
				FILING DATE September 1, 1999			
U.S. PATENT DOCUMENTS							
*Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
AA	5,383,011	4/1999	Lin et al				
AB	4,305,683	2/1989	Magdo et al				
AC	5,874,367	2/1999	Dobson				
AD	5,858,880	1/1999	Dobson et al				
AE	5,219,613	6/1993	Fabry et al				
AF	5,270,267	12/1993	Quellet				
AG	5,541,445	7/1996	Quellet				
AH	6,022,404	2/2000	Ettlinger et al				
AI	5,709,741	1/1998	Akamatsu et al				
AJ	4,648,904	3/1987	Depasquale et al				
AK	4,158,717	6/1979	Nelson				
AL	5,667,015	9/1997	Harestad et al				
AM	5,661,093	8/1997	Ravi et al				
AN	5,536,857	7/1996	Naula				
AO	4,695,859	9/1987	Guha et al				
AP	4,954,367	6/1990	Hosaka				
AQ	5,441,797	8/1995	Hogan				
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AS	5,759,755	6/1998	Park et al				
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AV	4,600,671	7/1986	Saitoh et al				

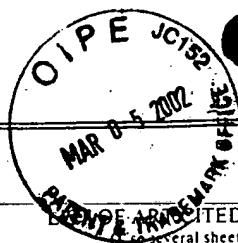
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Sheet 2 of 5

Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. MI22-1208		SERIAL NO. 09/388.826	
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U.S. PATENT DOCUMENTS							
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
	BA	5,753,326	5/1998	Mikoshiba et al.			
	BB	5,356,515	10/1994	Tahara et al.			
	BC	5,674,356	10/07/97	Nagayama			
	BD	5,731,242	03/24/98	Parat et al.			
	BE	5,741,721	04/21/98	Stevens			
	BF	5,034,348	07/23/91	Hartswick et al.			
	BG	5,472,829	12/05/95	Ogawa			
	BH	5,641,607	06/24/97	Ogawa et al.			
	BI	5,648,202	07/15/97	Ogawa et al.			
	BJ	5,670,297	09/23/97	Ogawa et al.			
	BK	5,677,111	10/14/97	Ogawa			
	BL	5,693,352	12/16/97	Ogawa et al.			
	BM	5,831,321	11/03/98	Nagayama			
	BN	5,591,566	01/07/97	Ogawa			
	BO	6,008,124	12/28/99	Sekiguchi et al.			
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	BQ	5,600,165	02/04/97	Tsukamoto et al.			
	BR	5,872,385	02/16/99	Taft et al.			
	BS	5,960,289	09/28/99	Tsui et al.			
	BT	5,968,324	10/19/99	Cheung et al.			
	BU	6,020,243	02/01/00	Wallace et al.			
	BV	5,472,327	12/1995	Ogawa et al.			
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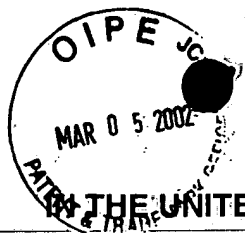
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U.S. PATENT DOCUMENTS							
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	CA	4,474,975	10-84	Clemons et al.			
	CB	5,962,581	10-99	Hayase et al.			
	CC	6,140,151	10-00	Akram			
	CD	5,314,724	5-94	Tsukune et al.			
	CE	5,376,391	12-94	Maeda et al.			
	CF	5,817,549	10-98	Yamazaki et al.			
	CG	6,072,227	6-00	Yau et al.			
	CH	6,001,741	12-99	Alers			
	CI	5,786,039	7-98	Brouquet			
	CJ	6,235,568 B1	5-01	Murthy			
	CK	6,187,694 B1	2-01	Cheng			
	CL	5,750,442	5-98	Juengling			
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	CN	6,238,976	5-01	Noble			
	CO	6,008,121	12-99	Yang			
	CP	5,140,390	8-92	Li			
	CQ	5,286,661	2-94	de Fresart			
	CR	6,184,151	2-01	Adair			
	CS	6,225,217 B1	5-01	Usami			
	CT	6,004,850	12-99	Lucas			
	CU	6,140,677	10-00	Gardner			
	CV	6,133,096	10-00	Su			
	CW	6,136,636	10-00	Wu			
	CX	5,933,721	8-99	Hause			
	CY	5,981,368	11-99	Gardner			
	CZ	6,159,804	12-00	Gardner			
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	C2	6,235,591	5-01	Balasubramanian			
	C3	6,193,144 B1	3-01	Pan			
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LIST-OF-ART-CITED-BY-APPLICANT (Use several sheets if necessary)				APPLICANT Weimin Li et al.	
				FILING DATE September 1, 1999	GROUP 2813
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)					
	EA	TEXT: Jenkins, F. et al., "Fundamentals of Optics", Properties of Light, pp. 9-10. (No date)			
	EB	TEXT: Wolf, S. et al., "Silicon Processing for the VLSI Era", Vol. 1, pp. 437-441. (No date)			
		D.R. McKenzie et al., "New Technology for PACVD", Surface and Coatings Technology, 82 (1996), pp. 326-333.			
		S. McClatchie et al., "Low Dielectric Constant Flowfill® Technology For IMD Applications"; undated; 7 pages			
	EF	K. Beekmann et al., "Sub-micron Gap Fill and In-Situ Planarisation using Flowfill™ Technology"; October 1995; pp. 1-7			
	EH	A. Kiermasz et al., "Planarisation for Sub-Micron Devices Utilising a New Chemistry"; Electrotech, February 1995; 2 pages			
	EI	IBM Technical Disclosure Bulletin "Low-Temperature Deposition of SiO ₂ , Si ₃ N ₄ or SiO ₂ -Si ₃ N ₄ ," Vol. 28, No. 9, p. 4170, Feb. 1986.			
	EJ	ARTICLE: Bencher, C. et al., "Dielectric antireflective coatings for DUV lithography", Solid State Technology (March 1997), pp.109-114.			
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	EL	Ralls, Kenneth M., "Introduction to Materials Science and Engineering", John Wiley & Sons, © 1976, pp. 312-313			
	EM	Ravi K. Laxman, "Synthesizing Low-k CVD Materials for Fab Use", Semiconductor International, Nov. 2000, 10 pps.			
	EN	Anonymous, "New gas helps make faster IC's. Machine Design Cleveland, © Penton Media, Inc., November 4, 1999, pp. 118.			
	EO	Lobada et al., "Using Trimethylsilane to Improve Safety Throughput and Versatility in PECVD Processes", 4th International Symposium on Silicon Nitride and Silicon Dioxide Thin Insulating Films, The Electrochemical Society, Abstract No. 358, p. 454, May 1997.			
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	EQ	TEXT: Heavens, O. S., "Optical Properties of Thin Solid Films", pp. 48-49.			
	ER	Withmall, R. et al., "Matrix Reactions of Methylsilanes and Oxygen Atoms", Phys. Chem 1983, pp. 594-602.			
	ES	Weidman, T. et al., "New photodefinable glass etch masks for entirely dry photolithography: Plasma deposited organosilicon hydride polymers", Appl. Phys. Lett 1-25-93, pp. 372-374.			
	ET	Weidman, et al., "All Dry Lithography: Applications of Plasma Polymerized Methylsilane as a Single Layer Resist and Silicon Dioxide Precursor", Journal of Photopolymer Science and Technology, V. 8, #4, 1995, pp. 679-686.			
	EU	Joubert et al., "Application of Plasma Polymerized Methylsilane in an all dry resist process for 193 and 248 nm Lithography", Microelectronic Engineering 30 (1996), pp. 275-278.			
	EV	Joshi, A.M. et al., "Plasma Deposited Organosilicon Hydride Network Polymers as Versatile Resists for Entirely Dry Mid-Deep UV Photolithography, SPIE Vol. 1925, pp. 709-720.			
	EW	Matsuura, M. et al., "Highly Reliable Self-Planarizing Low-k Intermetal Dielectric for Sub-quarter Micron Interconnects", IEEE 1997, pp. 785-788.			
	EX	Horie, O. et al., "Kinetics and Mechanism of the Reactions of J. Phys. Chem 1991, 4393-4400.			
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SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Reference - - See attached Form PTO-1449

In compliance with 37 C.F.R. §§ 1.56, 1.97 and 1.98, your attention is directed to the United States patent listed on the attached Form PTO-1449. No admission is made regarding whether the submitted reference is prior art.

Citation of this reference is respectfully requested.

Respectfully submitted,

Date:

Mar 25, 2002

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